MC14503B

Hex Non-Inverting 3-State Buffer

The MC14503B is a hex non−inverting buffer with 3−state outputs, and a high current source and sink capability. The 3−state outputs make it useful in common bussing applications. Two disable controls are provided. A high level on the Disable A input causes the outputs of buffers 1 through 4 to go into a high impedance state and a high level on the Disable B input causes the outputs of buffers 5 and 6 to go into a high impedance state.

- 3−State Outputs
- TTL Compatible — Will Drive One TTL Load Over Full Temperature Range
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Two Disable Controls for Added Versatility
- Pin for Pin Replacement for MM80C97 and 340097

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 2.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}	Input Current (DC or Transient) per Pin	±10	mA
I_{out}	Output Current (DC or Transient) per Pin	±25	mA
P_D	Power Dissipation, per Package (Note 3.)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

2. Maximum Ratings are those values beyond which damage to the device may occur.
3. Temperature Derating:
   Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C

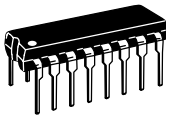
This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

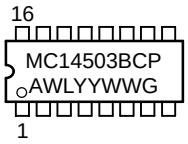
ON Semiconductor

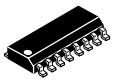
http://onsemi.com

MARKING DIAGRAMS

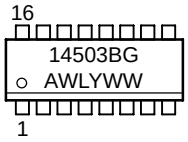


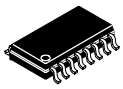
PDIP−16
P SUFFIX
CASE 648



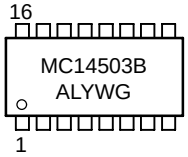


SOIC−16
D SUFFIX
CASE 751B





SOEIAJ−16
F SUFFIX
CASE 966



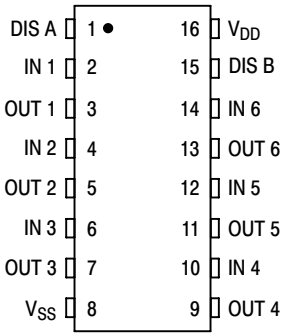
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb−Free Indicator

ORDERING INFORMATION

Device	Package	Shipping
MC14503BCP	PDIP−16	2000/Box
MC14503BD	SOIC−16	48/Rail
MC14503BDR2	SOIC−16	2500/Tape & Reel
MC14503BF	SOEIAJ−16	See Note 1.
MC14503BFEL	SOEIAJ−16	See Note 1.

1. For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

PIN ASSIGNMENT

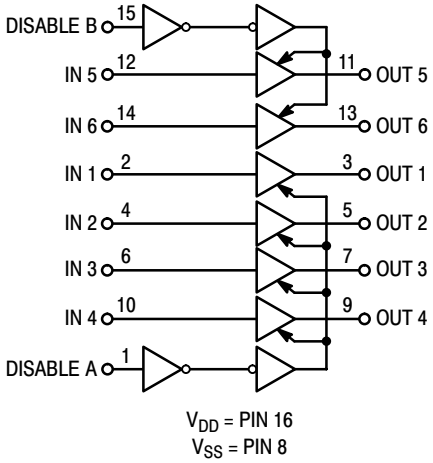


TRUTH TABLE

In_n	Appropriate Disable Input	Out_n
0	0	0
1	0	1
X	1	High Impedance

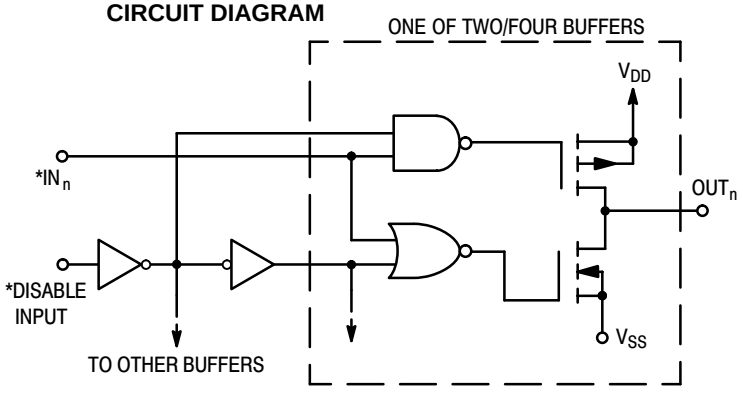
X = Don't Care

LOGIC DIAGRAM



V_{DD} = PIN 16
V_{SS} = PIN 8

CIRCUIT DIAGRAM



*Diode protection on all inputs (not shown)

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	− 55°C Min	− 55°C Max	25°C Min	25°C Typ (4.)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level	V_{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
V_{in} = 0		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
“1” Level	V_{OH}	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
V_{in} = V_{DD}		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage “0” Level	V_{IL}									Vdc
(V_O = 3.6 or 1.4 Vdc)		5.0	—	1.5	—	2.25	1.5	—	1.5	
(V_O = 7.2 or 2.8 Vdc)		10	—	3.0	—	4.50	3.0	—	3.0	
(V_O = 11.5 or 3.5 Vdc)		15	—	4.0	—	6.75	4.0	—	4.0	
“1” Level	V_{IH}									Vdc
(V_O = 1.4 or 3.6 Vdc)		5.0	3.5	—	3.5	2.75	—	3.5	—	
(V_O = 2.8 or 7.2 Vdc)		10	7.0	—	7.0	5.50	—	7.0	—	
(V_O = 3.5 or 11.5 Vdc)		15	11	—	11	8.25	—	11	—	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		4.5	– 4.3	—	– 3.6	– 5.0	—	– 2.5	—	
(V_{OH} = 2.5 Vdc)		5.0	– 5.8	—	– 4.8	– 6.1	—	– 3.0	—	
(V_{OH} = 4.6 Vdc)		5.0	– 1.2	—	– 1.02	– 1.4	—	– 0.7	—	
(V_{OH} = 9.5 Vdc)		10	– 3.1	—	– 2.6	– 3.7	—	– 1.8	—	
(V_{OH} = 13.5 Vdc)		15	– 8.2	—	– 6.8	– 14.1	—	– 4.8	—	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	4.5	2.2	—	1.8	2.1	—	1.2	—	mAdc
(V_{OL} = 0.4 Vdc)		5.0	2.6	—	2.1	2.3	—	1.3	—	
(V_{OL} = 0.5 Vdc)		10	6.5	—	5.5	6.2	—	3.8	—	
(V_{OL} = 1.5 Vdc)		15	19.2	—	16.1	25	—	11.2	—	
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_Q	5.0	—	1.0	—	0.002	1.0	—	30	µAdc
		10	—	2.0	—	0.004	2.0	—	60	
		15	—	4.0	—	0.006	4.0	—	120	
Total Supply Current (5.) (6.) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs) (All outputs switching, 50% Duty Cycle)	I_T	5.0	I_T = (2.5 µA/kHz) f + I_{DD}							µAdc
		10	I_T = (6.0 µA/kHz) f + I_{DD}							
		15	I_T = (10 µA/kHz) f + I_{DD}							
Three−State Output Leakage Current	I_{TL}	15	—	± 0.1	—	± 0.0001	± 0.1	—	± 3.0	µAdc

4. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
5. The formulas given are for the typical characteristics only at 25°C.
6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.006.

SWITCHING CHARACTERISTICS [7.] (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} V_{CC}	All Types		Unit
			Typ [8.]	Max	
Output Rise Time	t_{TLH}				ns
t_{TLH} = (0.5 ns/pF) C_L + 20 ns		5.0	45	90	
t_{TLH} = (0.3 ns/pF) C_L + 8.0 ns		10	23	45	
t_{TLH} = (0.2 ns/pF) C_L + 8.0 ns		15	18	35	
Output Fall Time	t_{THL}				ns
t_{THL} = (0.5 ns/pF) C_L + 20 ns		5.0	45	90	
t_{THL} = (0.3 ns/pF) C_L + 8.0 ns		10	23	45	
t_{THL} = (0.2 ns/pF) C_L + 8.0 ns		15	18	35	
Turn−Off Delay Time, all Outputs	t_{PLH}				ns
t_{PLH} = (0.3 ns/pF) C_L + 60 ns		5.0	75	150	
t_{PLH} = (0.15 ns/pF) C_L + 27 ns		10	35	70	
t_{PLH} = (0.1 ns/pF) C_L + 20 ns		15	25	50	
Turn−On Delay Time, all Outputs	t_{PHL}				ns
t_{PHL} = (0.3 ns/pF) C_L + 60 ns		5.0	75	150	
t_{PHL} = (0.15 ns/pF) C_L + 27 ns		10	35	70	
t_{PHL} = (0.1 ns/pF) C_L + 20 ns		15	25	50	
3−State Propagation Delay Time	t_{PHZ}	5.0	75	150	ns
Output “1” to High Impedance		10	40	80	
		15	35	70	
Output “0” to High Impedance	t_{PLZ}	5.0	80	160	ns
		10	40	80	
		15	35	70	
High Impedance to “1” Level	t_{PZH}	5.0	65	130	ns
		10	25	50	
		15	20	40	
High Impedance to “0” Level	t_{PZL}	5.0	100	200	ns
		10	35	70	
		15	25	50	

7. The formulas given are for the typical characteristics only at 25°C.
8. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

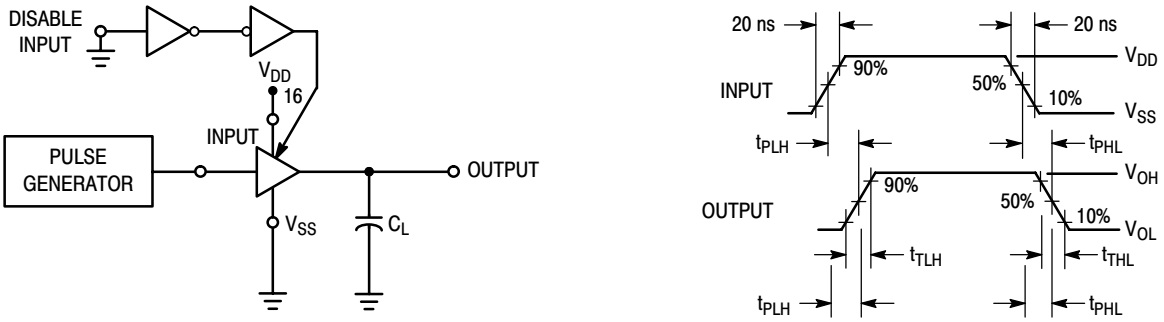


Figure 1. Switching Time Test Circuit and Waveforms (t_{TLH}, t_{THL}, t_{PHL}, and t_{PLH})

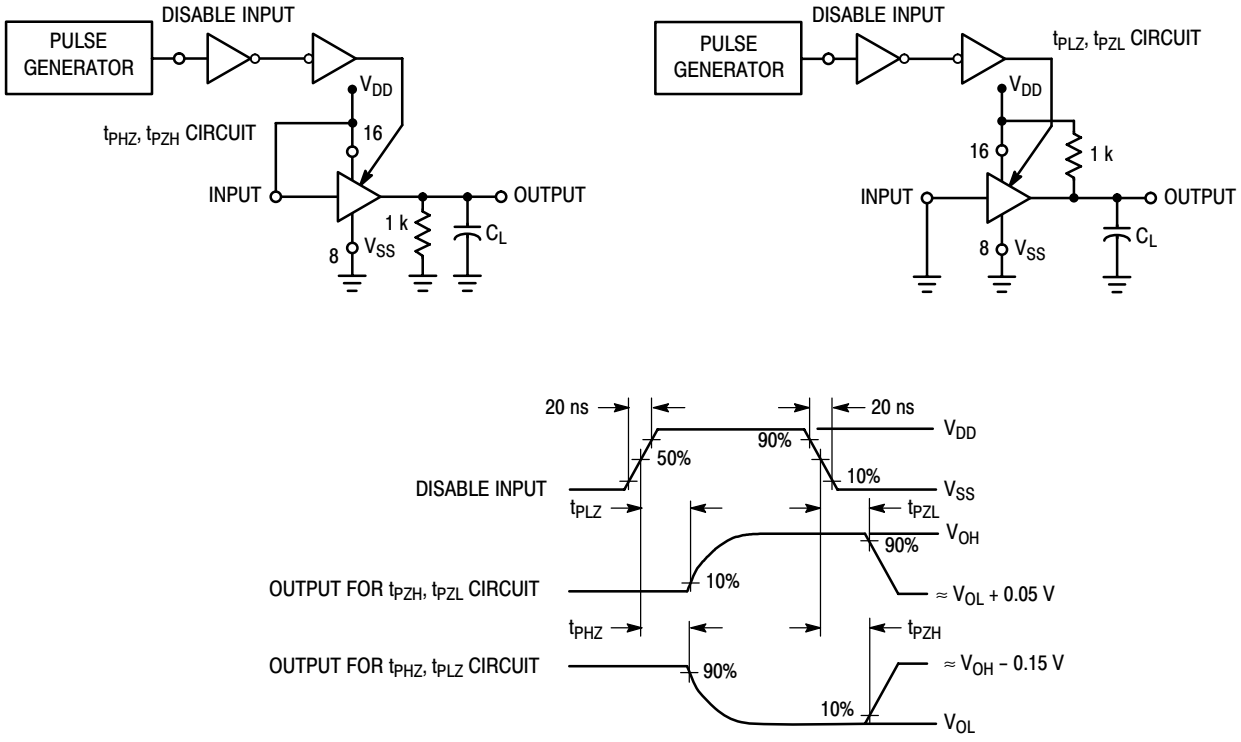
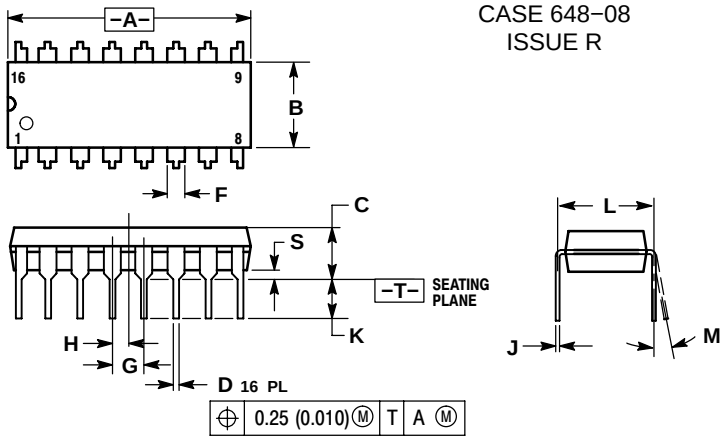


Figure 2. 3−State AC Test Circuit and Waveforms (t_{PLZ}, t_{PHZ}, t_{PZH}, t_{PZL})

PACKAGE DIMENSIONS

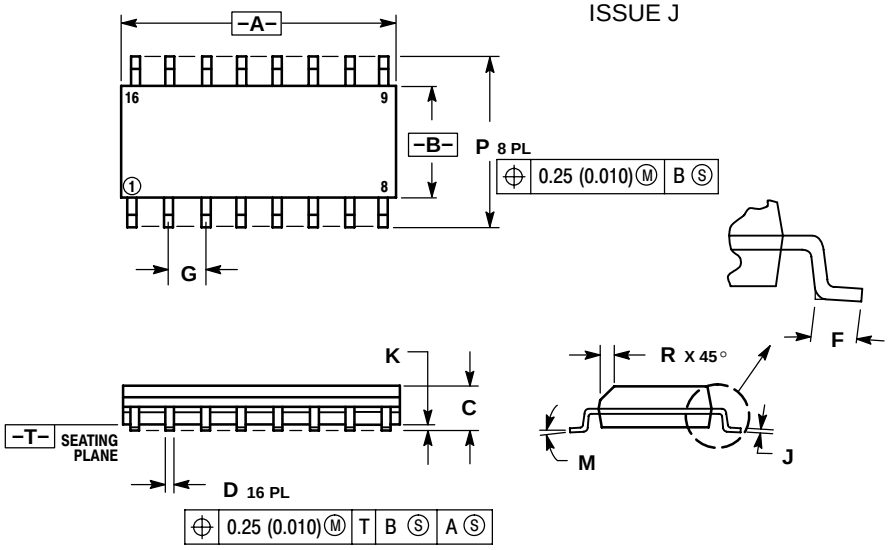
PDIP−16
P SUFFIX
PLASTIC DIP PACKAGE
CASE 648−08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

SOIC−16
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B−05
ISSUE J

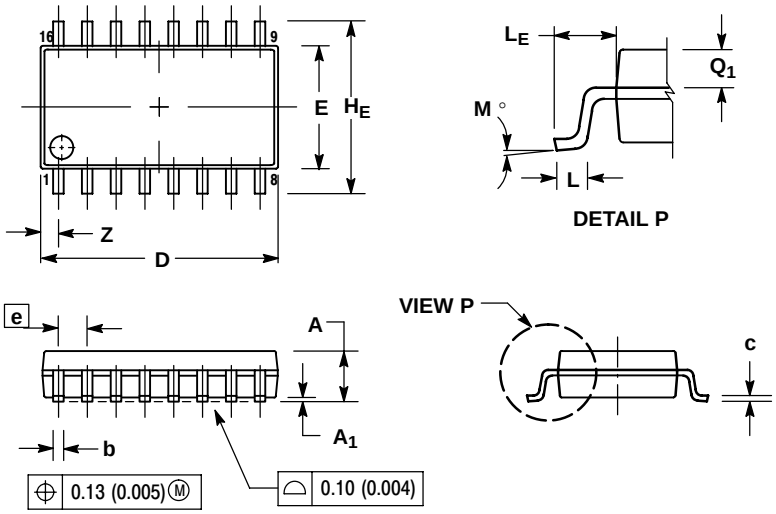


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

SOEIAJ−16
F SUFFIX
PLASTIC EIAJ SOIC PACKAGE
CASE 966−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
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ON Semiconductor Website: http://onsemi.com

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